

60V N-Channel Enhancement-Mode MOSFET

FEATURES

- $R_{DS(ON)} \leq 100m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} \leq 130m\Omega @ V_{GS}=4.5V$
- $R_{DS(ON)} \leq 200m\Omega @ V_{GS}=3.3V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- Capable doing Cu wire bonding
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

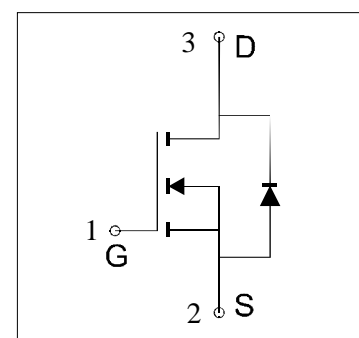
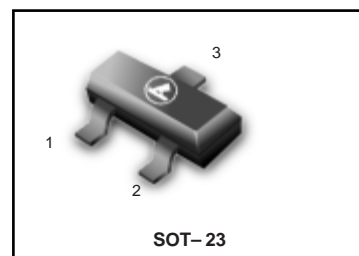
APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- Load Switch
- DSC

Ordering Information

| Device | Marking | Shipping |
|----------------------------|---------|-----------------|
| LN2308LT1G S-LN2308LT1G | N08 | 3000/Tape&Reel |
| LN2308LT3G S-LN2308LT3G | N08 | 10000/Tape&Reel |

LN2308LT1G
S-LN2308LT1G



Absolute Maximum Ratings (TA=25°C Unless Otherwise Noted)

| Parameter | | Symbol | Limit | Unit |
|---------------------------------------|-------------------------|-----------------|----------|------|
| Drain-Source Voltage | | V_{DSS} | 60 | V |
| Gate-Source Voltage | | V_{GSS} | ± 20 | V |
| Continuous Drain Current (tJ=150°C) | $T_A=25^\circ C$ | I_D | 2.6 | A |
| | $T_A=70^\circ C$ | | 1.8 | |
| Pulsed Drain Current | | I_{DM} | 8 | |
| Maximum Body-Diode Continuous Current | | I_S | 1.6 | A |
| Maximum Power Dissipation | $T_A=25^\circ C$ | P_D | 0.7 | W |
| | $T_A=70^\circ C$ | | 0.45 | |
| Operating Junction Temperature | | T_J | 150 | °C |
| Maximum Junction-to-Ambient | $T \leq 10 \text{ sec}$ | R_{thJA} | 150 | °C/W |
| | Steady State | | 175 | |
| Thermal Resistance-Junction to Case | | $R_{\theta JC}$ | 120 | °C/W |

*The device mounted on 1in² FR4 board with 2 oz copper

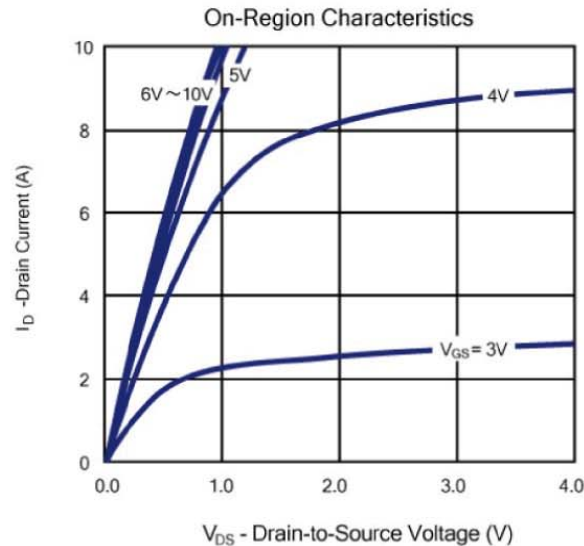
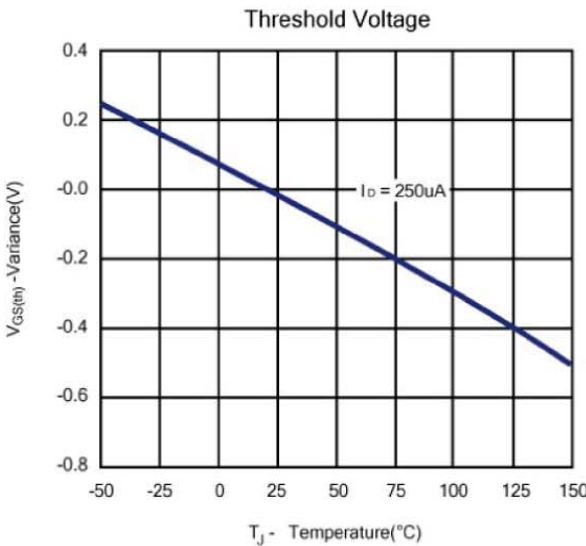
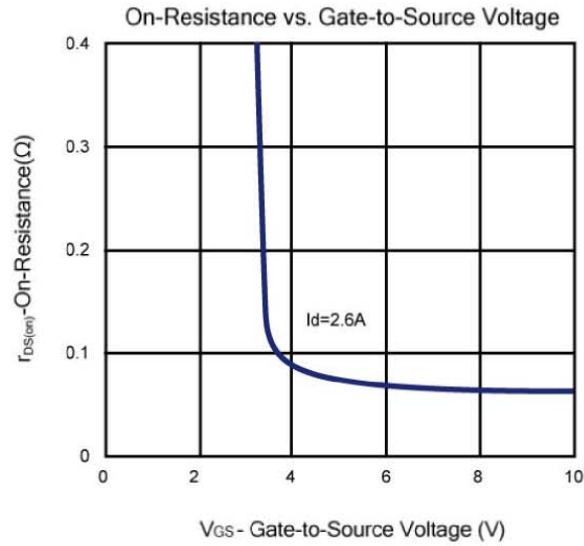
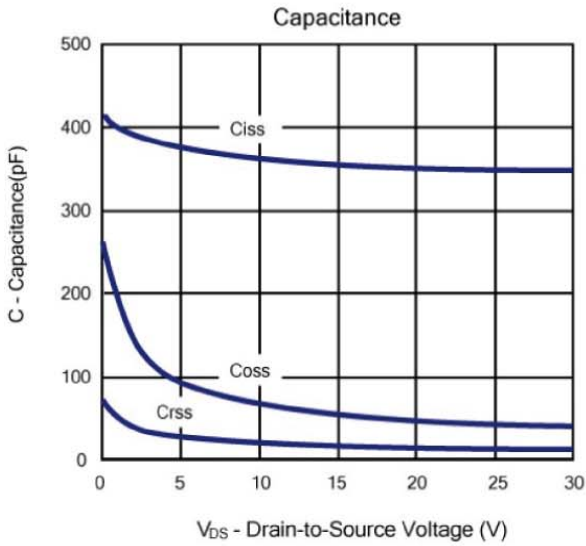
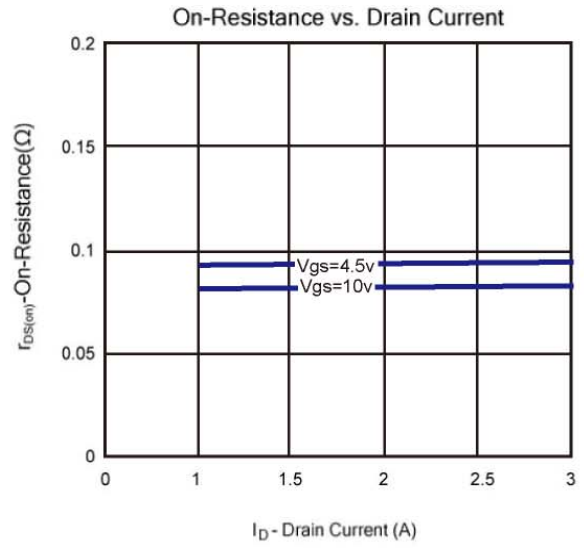
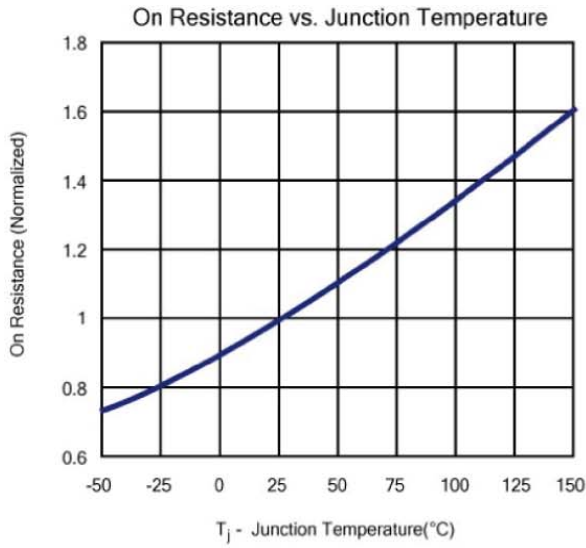
Electrical Characteristics ($T_a=25^{\circ}\text{C}$ Unless Otherwise Specified)

| Symbol | Parameter | Limit | Min | Typ | Max | Unit |
|----------------|---------------------------------|--|-----|-----|-----------|---------------|
| STATIC | | | | | | |
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS}=0, I_D=250\ \mu\text{A}$ | 60 | | | V |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}, I_D=250\ \mu\text{A}$ | 1 | | 3 | V |
| I_{GSS} | Gate Body Leakage | $V_{DS}=0V, V_{GS}=\pm 20V$ | | | ± 100 | nA |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS}=60V, V_{GS}=0V$ | | | 1 | μA |
| $R_{DS(ON)}$ | Drain-Source On-Resistance | $V_{GS}=10V, I_D=2.6A$ | | 82 | 100 | m Ω |
| | | $V_{GS}=4.5V, I_D=2.1A$ | | 96 | 130 | |
| | | $V_{GS}=3.3V, I_D=1.8A$ | | 139 | 200 | |
| V_{SD} | Diode Forward Voltage | $I_S=1.0A, V_{GS}=0V$ | | 0.8 | 1.2 | V |
| DYNAMIC | | | | | | |
| Q_g | Total Gate Charge | $V_{DS}=30V, V_{GS}=10V, I_D=2.6A$ | | 12 | | nC |
| Q_g | Total Gate Charge | $V_{DS}=30V, V_{GS}=4.5V, I_D=2.6A$ | | 6.5 | | |
| Q_{gs} | Gate-Source Charge | | | 2.2 | | |
| Q_{gd} | Gate-Drain Charge | | | 2.7 | | |
| C_{iss} | Input capacitance | $V_{DS}=30V, V_{GS}=0V, f=1\text{MHz}$ | | 350 | | pF |
| C_{oss} | Output Capacitance | | | 40 | | |
| C_{rss} | Reverse Transfer Capacitance | | | 12 | | |
| R_g | Gate Resistance | $V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$ | | 0.7 | | Ω |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD}=20V, R_L=20\ \Omega$ $I_D=1A, V_{GEN}=10V$ $R_G=1\ \Omega$ | | 10 | | ns |
| t_r | Turn-On Rise Time | | | 11 | | |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 29 | | |
| t_f | Turn-Off Fall Time | | | 3 | | |

 Notes: Pulse test; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

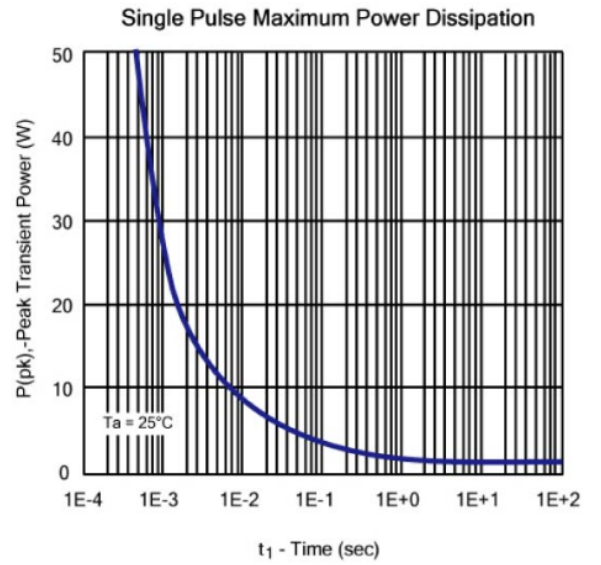
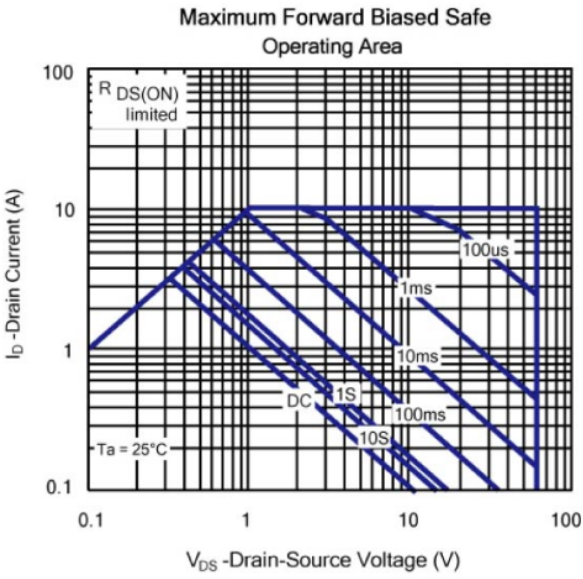
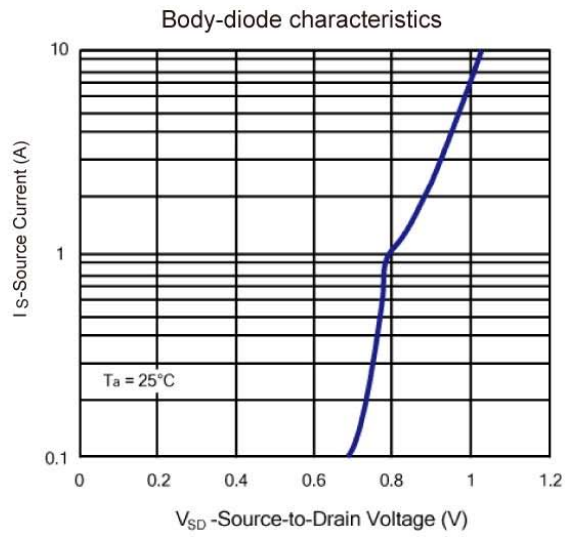
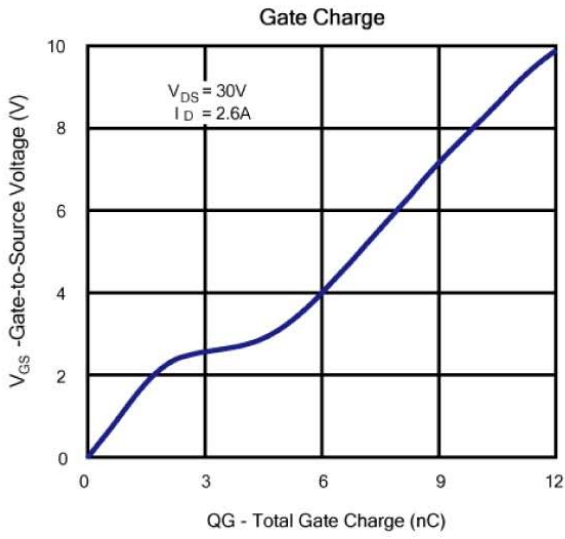
Typical Characteristics (Ta =25°C Noted)

LN2308LT1G , S-LN2308LT1G



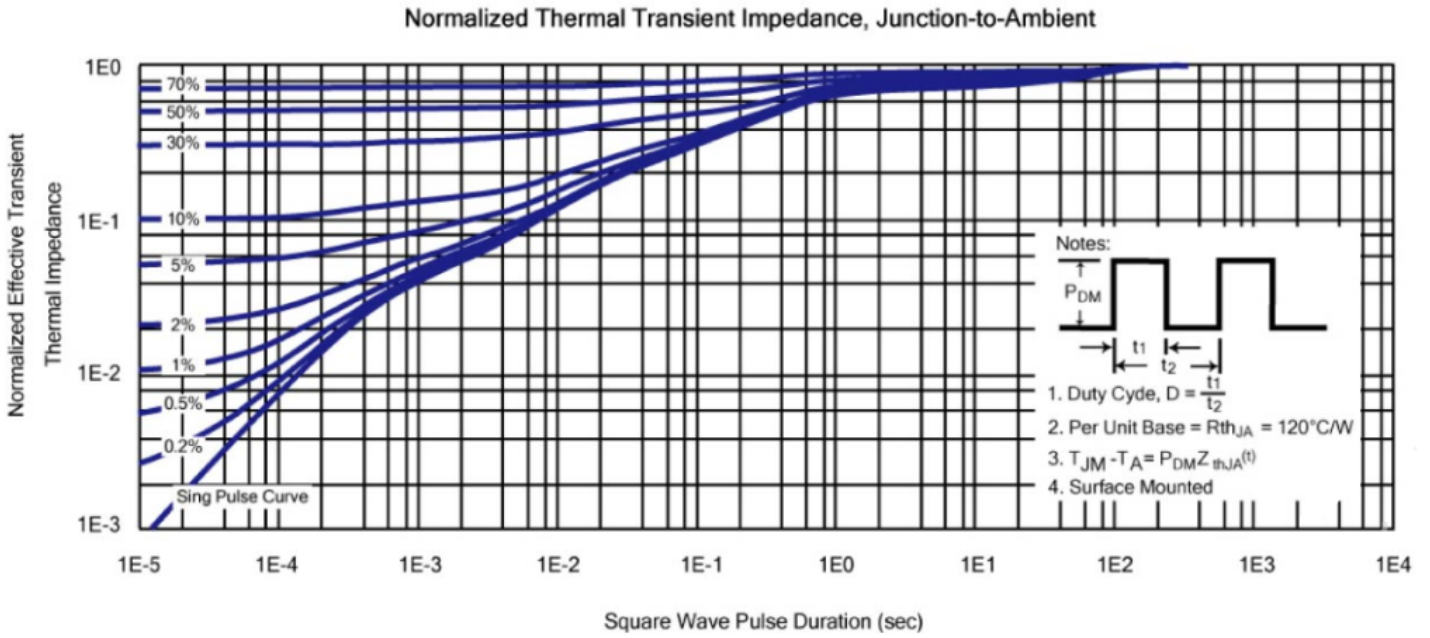
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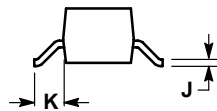
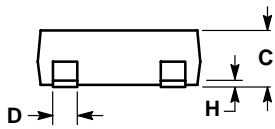
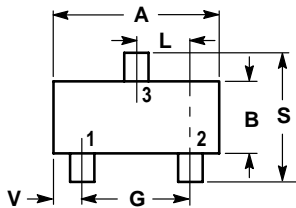


LN2308LT1G , S-LN2308LT1G

SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



| DIM | INCHES | | MILLIMETERS | |
|-----|--------|--------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.1102 | 0.1197 | 2.80 | 3.04 |
| B | 0.0472 | 0.0551 | 1.20 | 1.40 |
| C | 0.0350 | 0.0440 | 0.89 | 1.11 |
| D | 0.0150 | 0.0200 | 0.37 | 0.50 |
| G | 0.0701 | 0.0807 | 1.78 | 2.04 |
| H | 0.0005 | 0.0040 | 0.013 | 0.100 |
| J | 0.0034 | 0.0070 | 0.085 | 0.177 |
| K | 0.0140 | 0.0285 | 0.35 | 0.69 |
| L | 0.0350 | 0.0401 | 0.89 | 1.02 |
| S | 0.0830 | 0.1039 | 2.10 | 2.64 |
| V | 0.0177 | 0.0236 | 0.45 | 0.60 |

